TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

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SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS

HIGH SPEED DC-DC CONVERTER APPLICATIONS

• High Speed Switching $t_r=1.0\mu s$ (Max.), $t_f=1.0\mu s$ (Max.)

• High Collector Breakdown Voltage: VCEO=400V

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	500	V
Collector-Emitter Voltage	v_{CEO}	400	V
Emitter-Base Voltage	v_{EBO}	7	V
Collector Current	$^{\mathrm{I}}\mathrm{C}$	2	A
Base Current	$I_{\mathbf{B}}$	0.5	A
Collector Power Dissipation	$P_{\mathbf{C}}$	1.3	W
Junction Temperature	$\mathrm{T_{j}}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

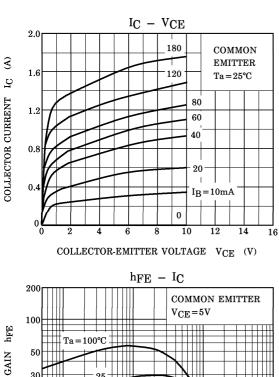
Unit in mm 8.0±0.2 1.4±0.1 1.05±0.1 1.5±0.1 1.5±0.1 2.5±0.5 2.5±0.5 1. EMITTER 2. COLLECTOR 3. BASE JEDEC JEITA TOSHIBA 2-8M1A

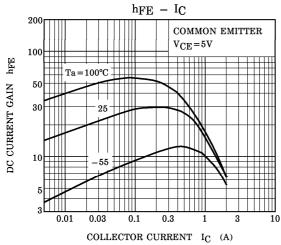
Weight: 0.55g (Typ.)

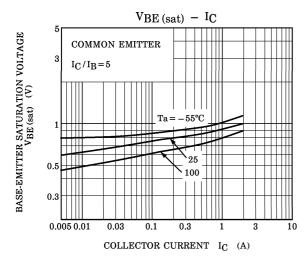
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

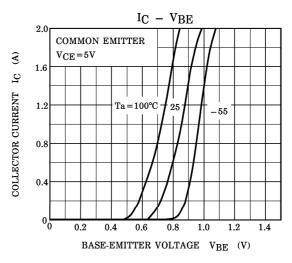
CHARA	ACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cu	ıt-off Current	I_{CBO}	$V_{CB} = 400V, I_{E} = 0$	_	_	100	μ A
Emitter Cut	-off Current	$I_{ m EBO}$	$V_{EB} = 7V, I_C = 0$	_	_	1	mA
Collector-Ba Voltage	se Breakdown	V _(BR) CBO	$I_{C}=1mA, I_{E}=0$	500	_	_	V
Collector-En Voltage	nitter Breakdown	V _(BR) CEO	$I_{C}=10mA, I_{B}=0$	400	_	_	V
DC Current Gain		h _{FE} (1)	$V_{CE} = 5V, I_{C} = 0.1A$	20	_	_	
		h _{FE (2)}	$V_{CE}=5V$, $I_{C}=1A$	8	_	_	
Saturation	Collector-Emitter	VCE (sat)	$I_C = 1A, I_B = 0.2A$	_	_	1.0	v
Voltage	Base-Emitter	V _{BE} (sat)	$I_C = 1A, I_B = 0.2A$	_	_	_ 1.5	\ \ \
Switching Stor	Rise Time	$\mathbf{t_r}$	20μs I _{B1} OUTPUT		_	1.0	
	Storage Time	$t_{ ext{stg}}$	Input o Input		_	2.5	μ s
	Fall Time	t_f	$I_{\text{B1}} = -I_{\text{B2}} = 0.08\text{A}$ DUTY CYCLE < 1% $V_{\text{CC}} = 200\text{V}$	_	_	1.0	

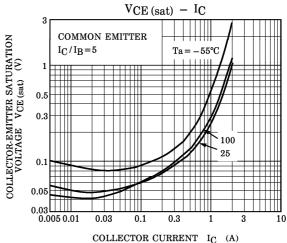
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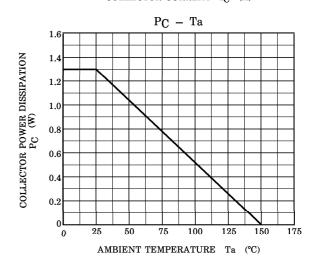




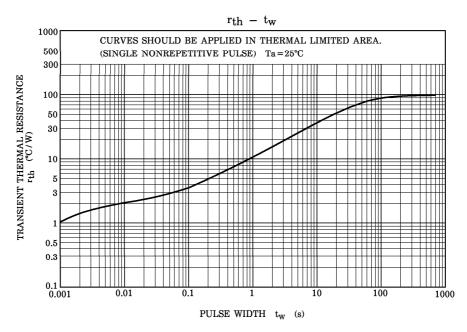


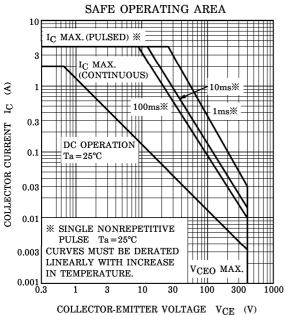






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